NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BLX14** is Designed for HF and VHF band applications.

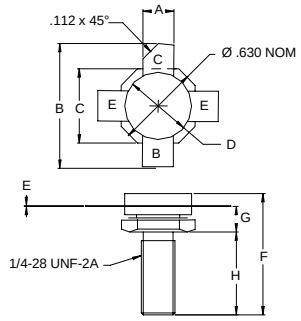
FEATURES:

- P_G = 13 dB min. at 15 W/1.6 MHz
- d_3 = -40 dB typ. at 15 W(PEP)
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	4.0 A
V_{CBO}	85 V
V_{EBO}	4.0 V
V_{CEO}	36 V
P_{DISS}	88 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	1.99 °C/W

PACKAGE STYLE .500 4L STUD (A)



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.050 / 26.67
C	.545 / 13.84	.555 / 14.10
D	.495 / 12.57	.505 / 12.83
E	.003 / 0.08	.007 / 0.18
F		.830 / 21.08
G	.185 / 4.70	.198 / 5.03
H	.497 / 12.62	.530 / 13.46

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I_C = 25 mA	85			V
BV_{CER}	I_C = 25 mA R_{BE} = 5.0 Ω	85			V
BV_{CEO}	I_C = 50 mA	36			V
BV_{EBO}	I_E = 10 mA	4.0			V
h_{FE}	V_{CE} = 6.0 V I_C = 1.4 A	15		100	---
f_T	V_{CE} = 20 V I_C = 3.0 A		250		MHz
C_C	V_{CB} = 30 V f = 1.0 MHz		115	125	pF
G_P	V_{CE} = 28 V I_{CQ} =2.0 A P_{OUT} = 15 W(PEP) f = 1.6 MHz	13			dB
d_3			-40		dB

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